

12A, 600V N-CHANNEL MOSFET

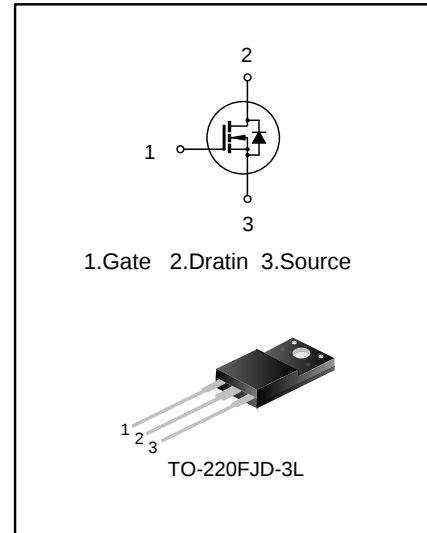
GENERAL DESCRIPTION

SVFP12N60CFJD is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ high-voltage planar VDMOS technology. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power supplies, DC-DC converters and H-bridge PWM motor drivers.

FEATURES

- ◆ 12A, 600V, $R_{DS(on)(typ.)}=0.58\Omega@V_{GS}=10V$
- ◆ Low gate charge
- ◆ Low Crss
- ◆ Fast switching
- ◆ Improved dv/dt capability



ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVFP12N60CFJD	TO-220FJD-3L	P12N60CFJD	Halogen free	Tube

ABSOLUTE MAXIMUM RATINGS (T_J=25°C, UNLESS OTHERWISE NOTED)

Characteristics		Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	600	V
Gate-Source Voltage		V _{GS}	±30	V
Drain Current	T _C =25°C	I _D	12	A
	T _C =100°C		7.6	
Drain Current Pulsed		I _{DM}	48	A
Power Dissipation(T _C =25°C) -Derate above 25°C		P _D	51	W
			0.41	W/°C
Single Pulsed Avalanche Energy (Note 1)		E _{AS}	798	mJ
Reverse Diode dv/dt (Note 2)		dv/dt	4.5	V/ns
MOSFET dv/dt Ruggedness (Note 3)		dv/dt	50	V/ns
Operation Junction Temperature Range		T _J	-55~+150	°C
Storage Temperature Range		T _{stg}	-55~+150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	2.44	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_J=25°C, UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	600	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	--	--	1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =6.0A	--	0.58	0.75	Ω
Input Capacitance	R _g	f=1.0MHz	--	5.0	--	Ω
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	--	1367	--	pF
Output Capacitance	C _{oss}		--	152	--	
Reverse Transfer Capacitance	C _{rss}		--	14	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} =300V, I _D =12A, V _{GS} =10V, R _G =24Ω (Note 4, 5)	--	24	--	ns
Turn-on Rise Time	t _r		--	52	--	
Turn-off Delay Time	t _{d(off)}		--	88	--	
Turn-off Fall Time	t _f		--	48	--	
Total Gate Charge	Q _g	V _{DS} =480V, I _D =12A, V _{GS} =10V (Note 4, 5)	--	34	--	nC
Gate-Source Charge	Q _{gs}		--	10	--	
Gate-Drain Charge	Q _{gd}		--	15	--	

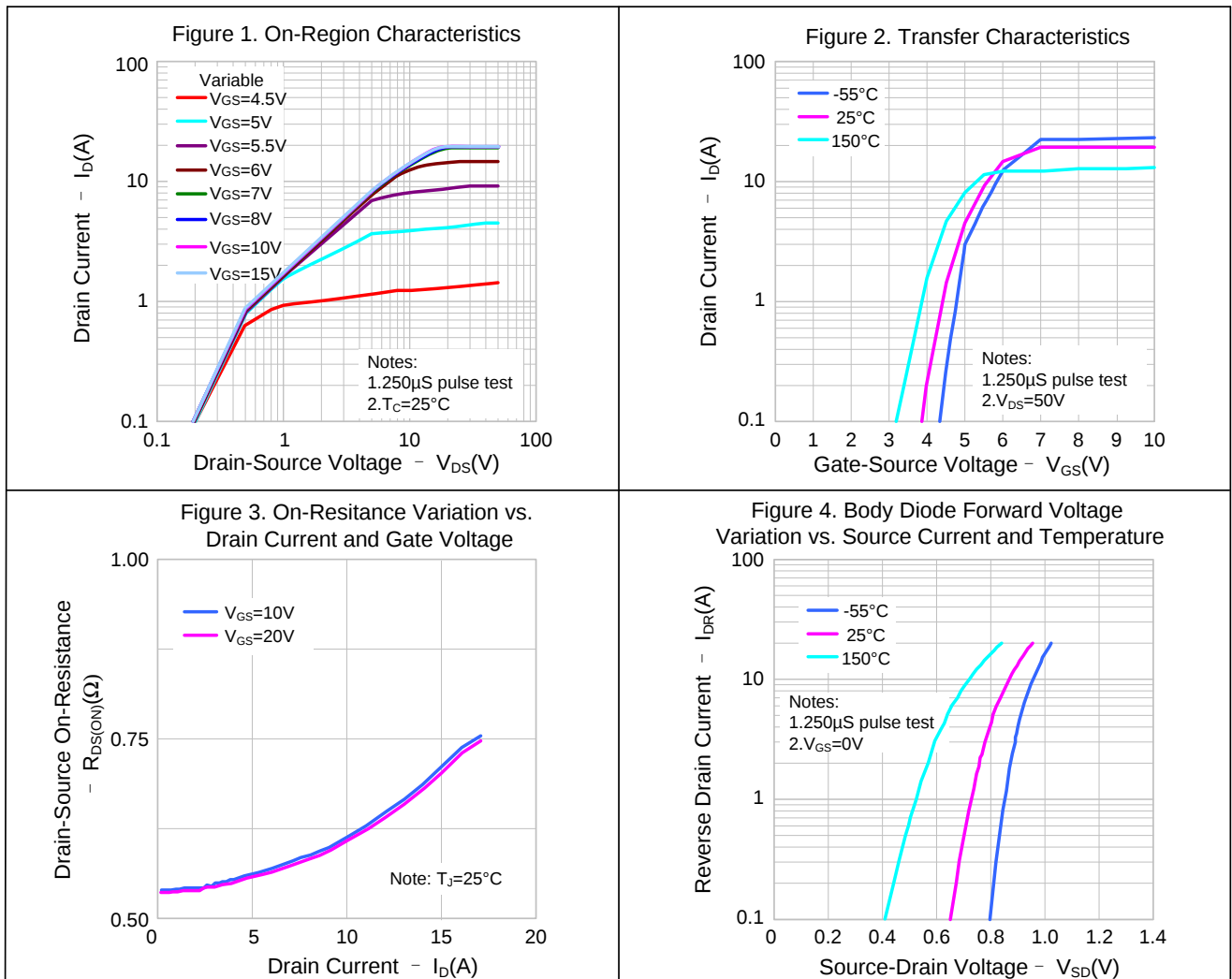
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse p-n Junction Diode in the MOSFET	--	--	12	A
Pulsed Source Current	I_{SM}		--	--	48	
Diode Forward Voltage	V_{SD}	$I_S=12A, V_{GS}=0V$	--	--	1.3	V
Reverse Recovery Time	T_{rr}	$I_S=12A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$ (Note 4)	--	530	--	ns
Reverse Recovery Charge	Q_{rr}		--	4.8	--	μC

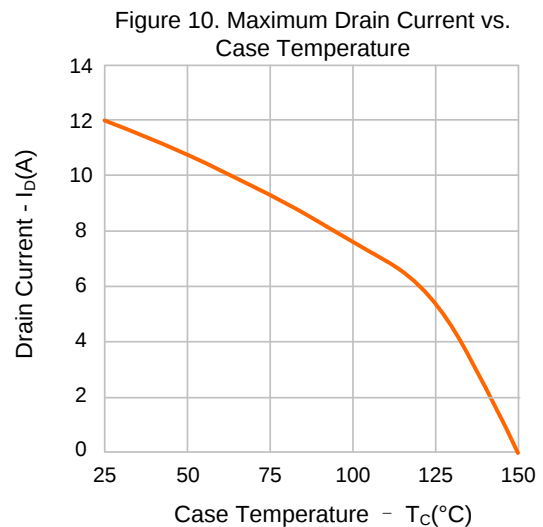
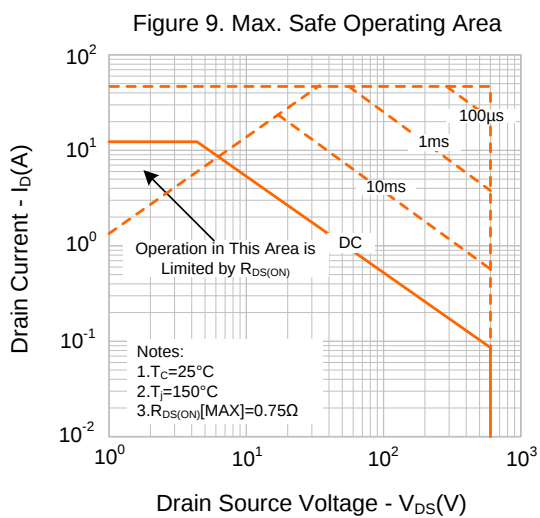
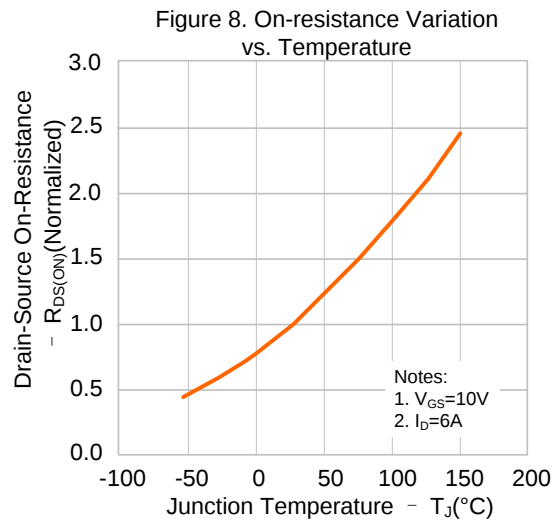
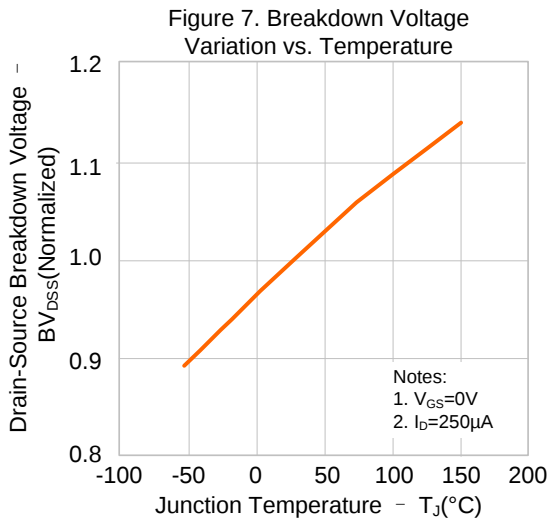
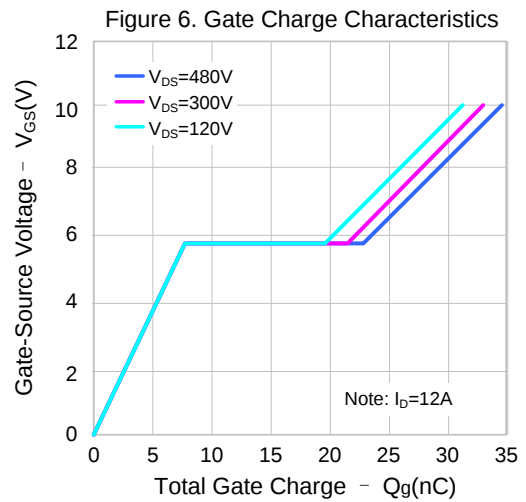
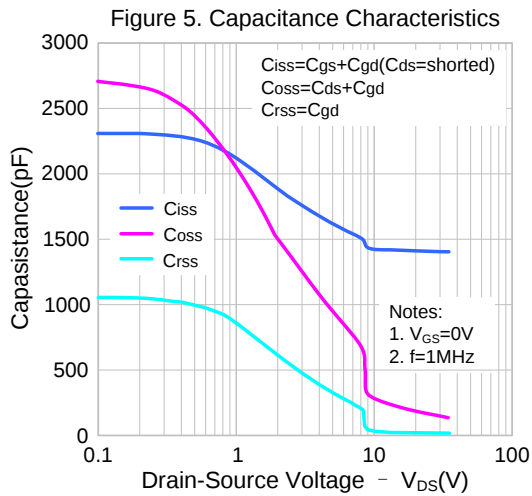
Notes:

1. $L=30mH, I_{AS}=6.66A, V_{DD}=100V, R_G=25\Omega$, starting temperature $T_J=25^\circ C$;
2. $V_{DS}=0\sim 400V, I_{SD}\leq 12A, T_J=25^\circ C$;
3. $V_{DS}=0\sim 480V$;
4. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;
5. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

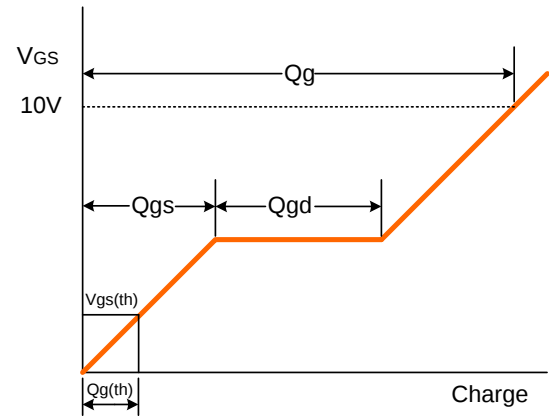
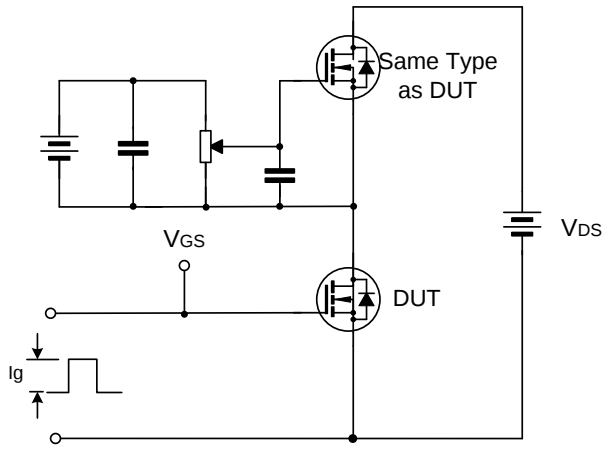


TYPICAL CHARACTERISTICS (CONTINUED)

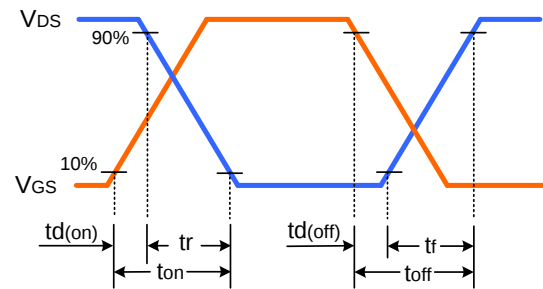
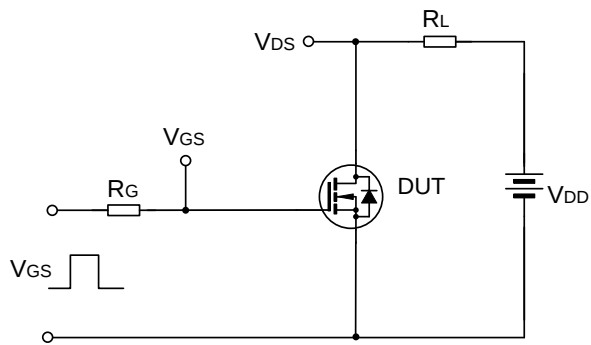


TYPICAL TEST CIRCUIT

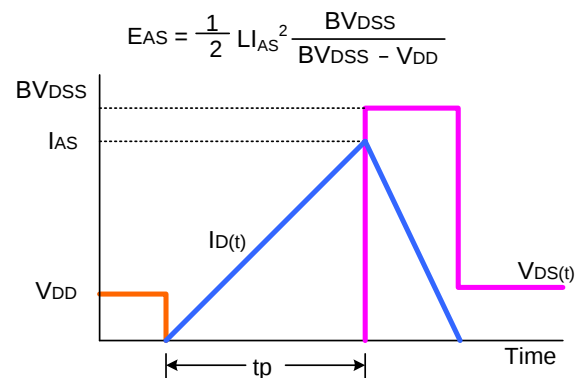
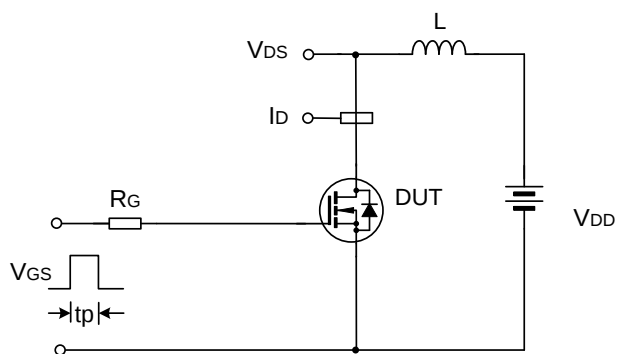
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



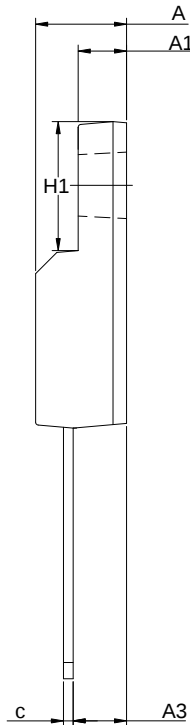
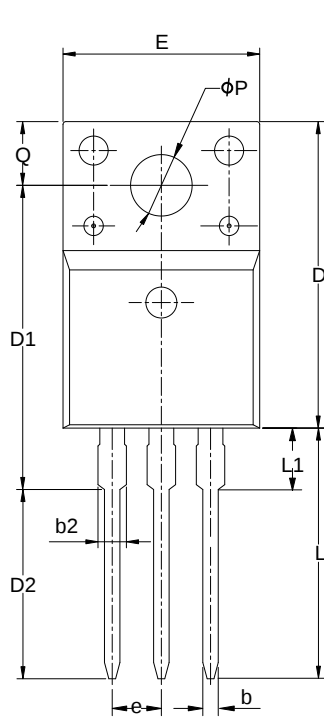
Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE

TO-220FJD-3L

UNIT: mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.55	0.70	0.85
b2	—	—	1.29
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	13.97	14.47	14.97
D2	10.58	11.08	11.58
E	9.73	10.16	10.36
e	2.54BSC		
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	—	—	2.00
ϕP	3.00	3.18	3.40
Q	3.05	3.30	3.55

Important notice :

1. The instructions are subject to change without notice!
2. Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current. Please read the instructions carefully before using our products, including the circuit operation precautions.
3. Our products are consumer electronic products or the other civil electronic products.
4. When using our products, please do not exceed the maximum rating of the products, otherwise the reliability of the whole machine will be affected. There is a certain possibility of failure or malfunction of any semiconductor product under specific conditions. The buyer is responsible for complying with safety standards and taking safety measures when using our products for system design, sample and whole machine manufacturing, so as to avoid potential failure risk that may cause personal injury or property loss.
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Rev.: 1.2

Revision History:

1. Modify electrical characteristics
 2. Update curve template
 3. Update package outline
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Rev.: 1.1

Revision History:

1. Modify Electrical schematic and TYPICAL TEST CIRCUIT
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Rev.: 1.0

Revision History:

1. First release
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